- Low $V_{CE(sat)}$.$V_{CE(sat)}$ ≤ -0.5V（I_C / I_B= -0.5A / -50mA）.
- I_C = -0.8A.
- PNP silicon transistor

Parameter	Symbol	Rating	Unit
Collector-base Voltage	V_{CBO}	-40	V
Collector-emitter Voltage	V_{CEO}	-32	V
Emitter-base Voltage	V_{EBO}	-5	V
Collector current	I_C	-0.8	A
Collector power dissipation	P_C	0.2	W
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	